

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2480	((438/455) or (438/458) or (438/479)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 16:24
S2	836	S1 and (soi or (silicon adj on adj insulator\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 17:39
S3	94	S2 and (((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) or epitaxial or (nitrogen adj dop\$3) or (hydrogen adj anneal\$3) or (intrinsic adj getter\$3)) near2 wafer\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 16:25
S4	23	S3 and (delaminat\$3 or (smart near2 cut))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 16:32
S5	1705	438/455	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 16:24
S6	2753	((438/455) or (438/458) or (438/479)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 16:24
S7	2753	((438/455) or (438/458) or (438/479)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 16:28
S8	947	S7 and (soi or (silicon adj on adj insulator\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 16:31

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S9	2	S8 and (((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) or epitaxial or (nitrogen adj dop\$3) or (hydrogen adj anneal\$3) or (intrinsic adj getter\$3)) near2 wafer\$1) near ((base or support or handle) near2 (wafer\$1 of substrate\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 16:29
S10	2	S7 and (((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) or epitaxial or (nitrogen adj dop\$3) or (hydrogen adj anneal\$3) or (intrinsic adj getter\$3)) near2 wafer\$1) near ((base or support or handle) near2 (wafer\$1 of substrate\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 16:30
S11	104	(((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) or epitaxial or (nitrogen adj dop\$3) or (hydrogen adj anneal\$3) or (intrinsic adj getter\$3)) near2 wafer\$1) near ((base or support or handle) near2 (wafer\$1 of substrate\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 17:00
S12	30	S11 and ("SOI" or (silicon adj on adj insulator\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 17:35
S13	3	S12 and (delaminat\$3 or (smart near2 cut))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 16:35
S14	3	S13 not S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 16:35
S15	0	S13 not S12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 16:35

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S16	27	S12 not S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 16:35
S17	66	((((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) or epitaxial or (nitrogen adj dop\$3) or (hydrogen adj anneal\$3) or (intrinsic adj getter\$3)) near2 wafer\$1) near ((base or support or handle) adj (wafer\$1 of substrate\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 17:01
S18	207	((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) or epitaxial or (nitrogen adj dop\$3) or (hydrogen adj anneal\$3) or (intrinsic adj getter\$3)) near10 ((base or support or handle) adj wafer\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 17:07
S19	34	S18 and S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 17:11
S20	2	((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) or epitaxial or (nitrogen adj dop\$3) or (hydrogen adj anneal\$3) or (intrinsic adj getter\$3)) adj ((base or support or handle) adj wafer\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 17:07
S21	147	((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) or epitaxial or (nitrogen adj dop\$3) or (hydrogen adj anneal\$3) or (intrinsic adj getter\$3)) near5 ((base or support or handle) adj wafer\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 17:30
S22	0	S19 not S18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 17:11

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S23	173	S18 not S19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 17:11
S24	40	((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) adj wafer\$1) or (epitaxial adj wafer\$1) or ((nitrogen adj dop\$3) adj wafer\$1) or ((hydrogen adj anneal\$3) adj wafer\$1) or ((intrinsic adj getter\$3) adj wafer\$1)) same ((base or support or handle) adj wafer\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 17:35
S25	34	S24 and ("SOI" or (silicon adj on adj insulator\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 17:36